

BT138X series D and E

12 A four-quadrant triacs, sensitive gate
Rev. 03 — 10 March 2008

Product data sheet

Product profile

1.1 General description

Passivated sensitive gate triac in a SOT186A full pack plastic package.

1.2 Features

- Very sensitive gate
- Direct interfacing to logic level ICs
- Isolated mounting base
- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits
- High isolation voltage

1.3 Applications

General purpose switching and phase control

230 V lamp dimmers

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BT138X-600D)}$
- $V_{DRM} \le 600 \text{ V (BT138X-600E)}$
- $V_{DRM} \le 800 \text{ V (BT138X-800E)}$
- $I_{GT} \le 5 \text{ mA (BT138X-600D)}$
- $I_{GT} \le 10 \text{ mA (BT138X-600E)}$
- $I_{GT} \le 10 \text{ mA (BT138X-800E)}$
- $I_{T(RMS)} \le 12 A$
- $I_{TSM} \le 95 \text{ A (t = 20 ms)}$
- $I_{GT} \le 10 \text{ mA } (T2-G+) (BT138X-600D)$
- $I_{GT} \le 25 \text{ mA } (T2-G+) \text{ (BT138X-600E)}$
- $I_{GT} \le 25 \text{ mA } (T2-G+) \text{ (BT138X-800E)}$



2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 1 (T1)		N 1
2	main terminal 2 (T2)	mb	T2—T1
3	gate (G)		`G sym051
mb	mounting base; isolated		
		SOT186A (TO-220F)	

3. Ordering information

Table 2. Ordering information

Type number	Package						
	Name	Description	Version				
BT138X-600D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole;	SOT186A				
BT138X-600E		3-lead TO-220 'full pack'					
BT138X-800E							

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

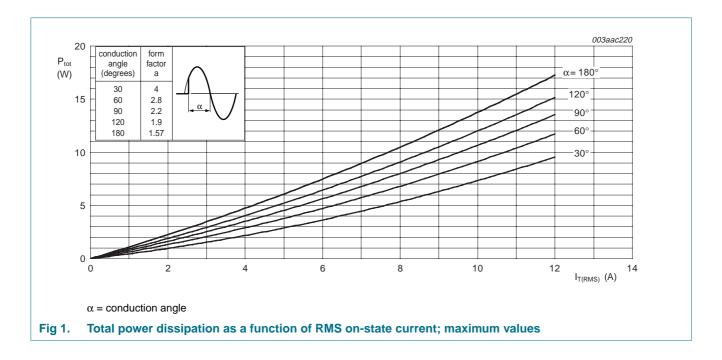
Parameter	Conditions	Min	Max	Unit
repetitive peak off-state voltage	BT138X-600D	[1] _	600	V
	BT138X-600E	[1] _	600	V
	BT138X-800E	-	800	V
RMS on-state current	full sine wave; $T_h \le 56$ °C; see Figure 4 and 5	-	12	Α
on-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
	t = 20 ms	-	95	Α
	t = 16.7 ms	-	105	Α
I ² t for fusing	t _p = 10 ms	-	45	A ² s
rate of rise of on-state current	$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$			
	T2+ G+	-	50	A/μs
	T2+ G-	-	50	A/μs
	T2- G-	-	50	A/μs
	T2- G+	-	10	A/μs
	RMS on-state current non-repetitive peak on-state current I ² t for fusing	$BT138X-600E \\ BT138X-800E \\ RMS \ on\text{-state current} \qquad full \ sine \ wave; \ T_h \le 56 \ ^\circ C; \\ see \ \underline{Figure 4} \ and \ \underline{5} \\ \hline non\text{-repetitive peak on-state current} \qquad full \ sine \ wave; \ T_j = 25 \ ^\circ C \ prior \ to \ surge; \\ see \ \underline{Figure 2} \ and \ \underline{3} \\ \hline t = 20 \ ms \\ \hline t = 16.7 \ ms \\ \hline I_{2} t \ for \ fusing \qquad t_p = 10 \ ms \\ \hline rate \ of \ rise \ of \ on\text{-state current} \qquad I_{TM} = 20 \ A; \ d_G/dt = 0.2 \ A/\mu s \\ \hline T2+ \ G- \\ \hline T2- \ G- \\ \hline T2- \ G- \\ \hline$		$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

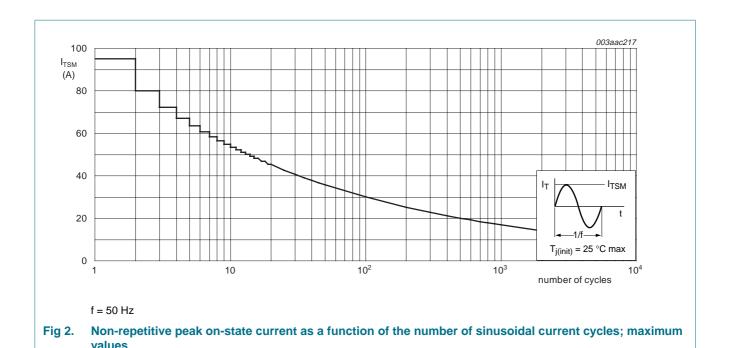
 Table 3.
 Limiting values ...continued

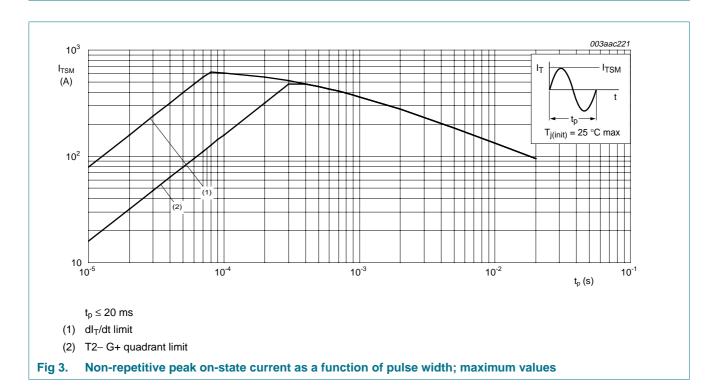
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{GM}	peak gate current		-	2	Α
P_GM	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	+150	°C
T _j	junction temperature		-	125	°C

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.







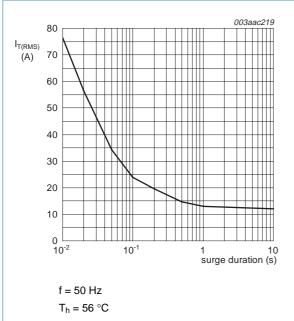


Fig 4. RMS on-state current as a function of surge duration; maximum values

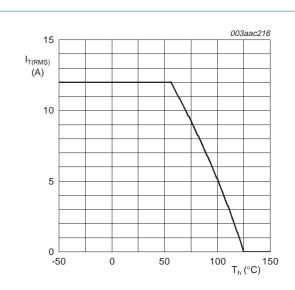
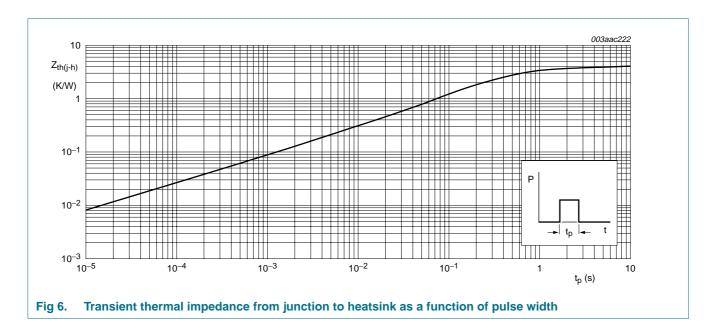


Fig 5. RMS on-state current as a function of heatsink temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle; see Figure 6	-	-	4.0	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; in free air	-	55	-	K/W



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all three terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz ; sinusoidal waveform; relative humidity $\leq 65 \text{ \%}$; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from pin 2 to external heatsink; f = 1 MHz	-	10	-	pF

7. Static characteristics

Table 6. Static characteristics

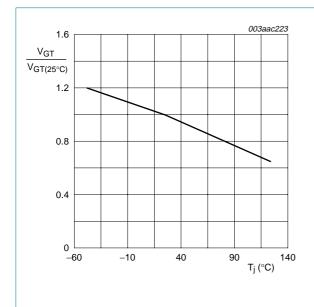
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol Parameter		Conditions		BT138X-600D		BT138X-600E BT138X-800E			Unit
			Min	Тур	Max	Min	Тур	Max	
I_{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } \frac{\text{Figure 8}}{}$							
		T2+ G+	-	1.3	5	-	2.5	10	mA
		T2+ G-	-	2.8	5	-	4.0	10	mA
		T2- G-	-	3.2	5	-	5.0	10	mA
		T2- G+	-	5.5	10	-	11	25	mA
I _L latching current		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 10}{\text{Figure } 10}$							
		T2+ G+	-	-	15	-	-	30	mA
		T2+ G-	-	-	20	-	-	40	mA
		T2- G-	-	-	15	-	-	30	mA
		T2- G+	-	-	20	-	-	40	mA
I _H	holding current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{\text{Figure } 11}$	-	-	10	-	-	30	mA
V_{T}	on-state voltage	I _T = 15 A; see <u>Figure 9</u>	-	1.4	1.65	-	1.4	1.65	V
V_{GT}	gate trigger voltage	$I_T = 0.1 \text{ A}$; see <u>Figure 7</u>							
		V _D = 12 V	-	0.7	1.5	-	0.7	1.5	V
		$V_D = V_{DRM}$; $T_j = 125 ^{\circ}C$	0.25	0.4	-	0.25	0.4	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	-	0.1	0.5	mA

8. Dynamic characteristics

Table 7. Dynamic characteristics

Symbol	Parameter	Conditions	BT138X-600D			BT138X-600E BT138X-800E			Unit
		Min	Тур	Max	Min	Тур	Max		
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)};$ exponential waveform; gate open circuit; $T_j = 125 ^{\circ}C$	-	50	-	-	150	-	V/μs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 16 \text{ A};$ $V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	-	2	-	μs



1 003aac224

1GT (25°C)

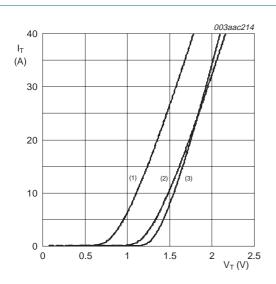
2 (3)
(4)
(4)
(1)
(2)
(3)
(4)
(4)
(4)
(7)
(°C)

- (1) T2-G+
- (2) T2-G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

BT138X_SER_D_E_3



 $V_0 = 1.175 \text{ V}$

 $R_s = 0.032 \Omega$

(1) $T_j = 125$ °C; typical values

(2) T_i = 125 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig 9. On-state current as a function of on-state voltage

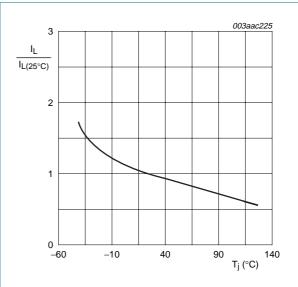


Fig 10. Normalized latching current as a function of junction temperature

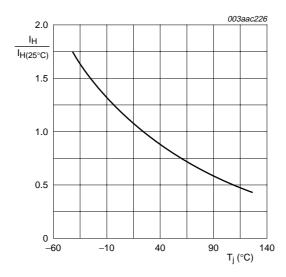
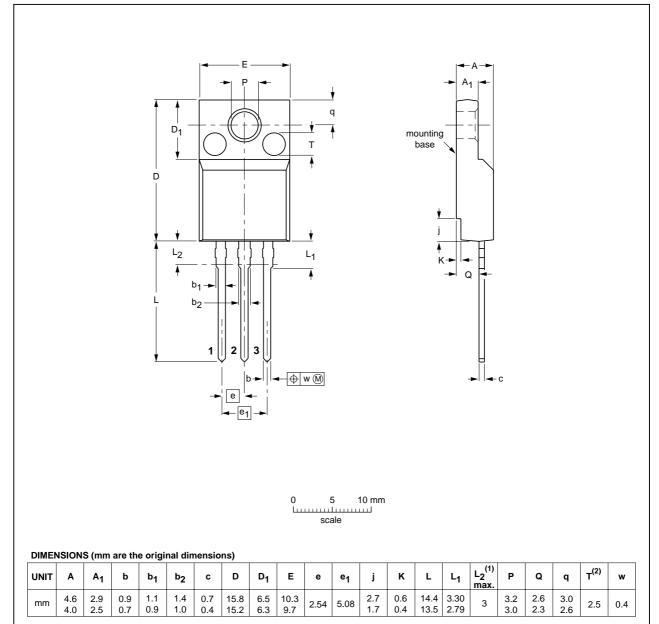


Fig 11. Normalized holding current as a function of junction temperature

9. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE	
SOT186A		3-lead TO-220F				-02-04-09 06-02-14	

Fig 12. Package outline SOT186A (TO-220F)

BT138X series D and E

12 A four-quadrant triacs, sensitive gate

10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT138X_SER_D_E_3	20080310	Product data sheet	-	BT138X_SERIES_E_2
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	 Legal texts I 	have been adapted to the ne	ew company name whe	ere appropriate.
	• BT138X-600	OD product added.		
	 Table 7 "Dyr 	namic characteristics": dV _D /	dt uprated for BT138X	series E.
BT138X_SERIES_E_2	20010601	Product data sheet	-	BT138X_SERIES_E_1
BT138X_SERIES_E_1	19970901	Product data sheet	-	-

BT138X series D and E

12 A four-quadrant triacs, sensitive gate

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

BT138X series D and E

12 A four-quadrant triacs, sensitive gate

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